

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ic	500	mA
Base Current	IB	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Rewer Dissipation	(Note 5)	D-	2	W	
Power Dissipation	(Note 6)	P _D	1	vv	
Thermal Desistance, Junction to Ambient	(Note 5)	R _{0JA}	62	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)		125		
Thermal Resistance, Junction to Leads (Note 7)		R _{θJL}	19.4	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-65 to +150	°C	

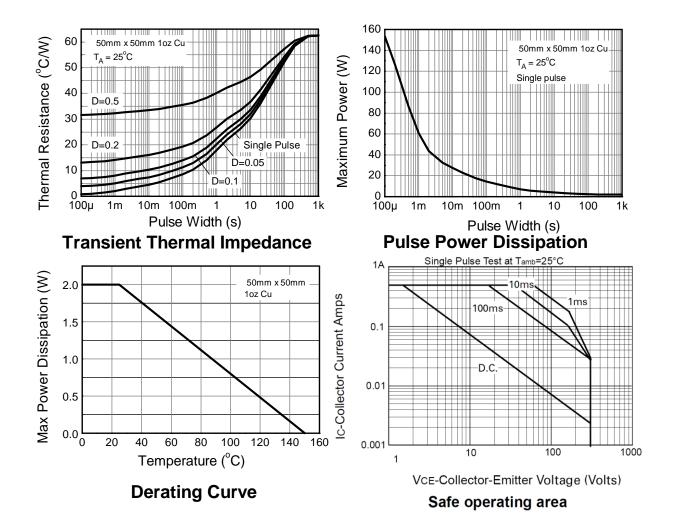
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on 50mm x 50mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured Notes: So hard a device inclusive modified with the collector lead on somm x somm to copper that is under still air conditions whilst operating in a steady-state.
Same as note (5), except mounted on minimum recommended pad (MRP) layout.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



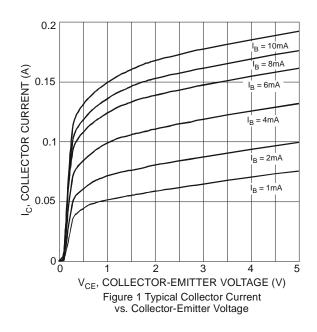


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS			•	•	•	
Collector-Base Breakdown Voltage	BV _{CBO}	300	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	300	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	_	V	I _E = 100μA
Collector-Base Cut-off Current	I _{CBO}	_	—	0.1	μA	V _{CB} = 200V
Emitter-Base Cut-off Current	I _{EBO}	_	—	0.1	μA	$V_{EB} = 6V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)			•			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	—	0.5	V	$I_C = 20mA$, $I_B = 2mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	—	0.9	V	$I_{C} = 20mA, I_{B} = 2mA$
		25	—	_		$I_{C} = 1mA, V_{CE} = 10V$
Static Forward Current Transfer Ratio	h _{FE}	40	_	_	—	$I_{C} = 10 mA$, $V_{CE} = 10 V$
		40	_	—		$I_{C} = 30 \text{mA}, V_{CE} = 10 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	50	_	—	MHz	$I_{C} = 10 \text{mA}, V_{CE} = 20 \text{V}$ $f = 100 \text{MHz}$
Output Capacitance	Cobo	_	_	3	pF	$V_{CB} = 20V, f = 1MHz$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



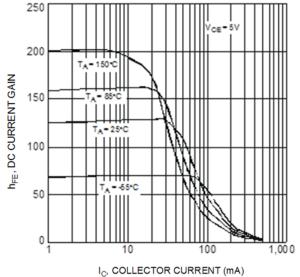


Figure 2 Typical DC Current Gain vs. Collector Current



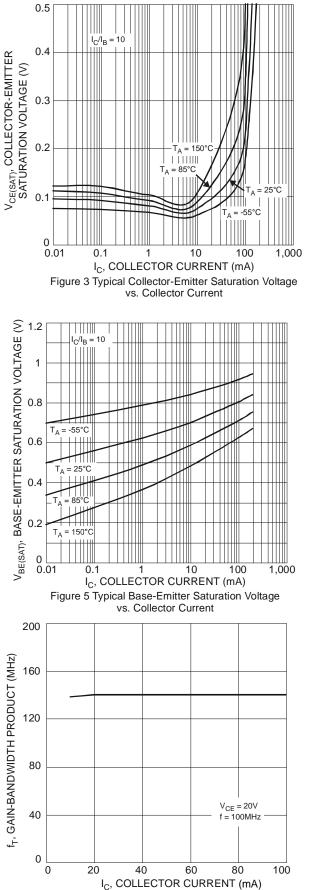


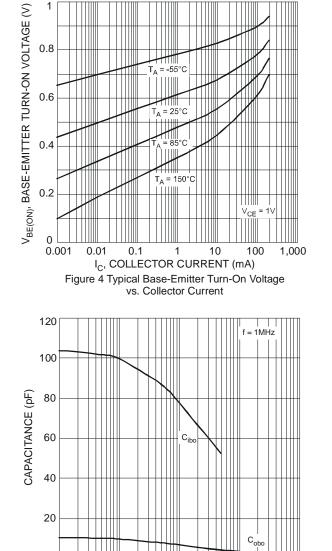
Figure 7 Typical Gain-Bandwidth Product vs. Collector Current



0

0.01

0.1



1

V_R, REVERSE VOLTAGE (V)

Figure 6 Typical Capacitance Characteristics

10

100

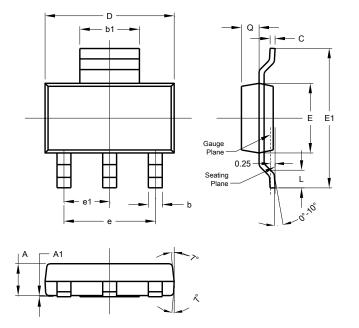


DZTA42

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

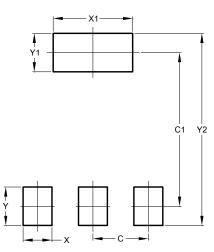
SOT223



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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